

ABSTRACT OF THE DISCLOSURE

The invention discloses a positive-working photoresist composition suitable for patterning light-exposure with light having a wavelength of 200 nm or shorter. The photoresist composition comprises a resinous compound capable of being imparted with increased solubility in an aqueous alkaline solution by interaction with an acid, a radiation-sensitive acid generating compound capable of generating an acid by irradiation with a radiation and an organic solvent, in which the resinous compound is a copolymer consisting of a combination of three types of specific (meth)acrylate units as the monomeric units. The patterned resist layer formed from the photoresist composition has an advantage in respect of decreased line slimming caused by electron beam irradiation in SEM inspection.

四庫全書